

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate[[,]] are a channel region, a source region, a drain region, a first insulating layer and a second insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

said glass substrate is defined as having a physical property such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute,

said first insulating layer covers said channel region and has a layer thickness whose lower limit is 4nm, and

said second insulating layer is formed on a surface of said first insulating layer.

**Claims 2-8. (Canceled)**

9. (Currently Amended) A thin-film transistor comprising:  
a glass substrate; and  
formed at an upper part of said glass substrate[[,]] are a channel region, a source region, a drain region and an insulating layer, wherein:  
said channel region, said source region and said drain region comprise polycrystalline silicon,  
said glass substrate is defined as having a physical property such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute, and  
said insulating layer covers said channel region and has a layer thickness defined by the range 4nm to 20nm.

**Claim 10. (Canceled)**

11. (Original) The thin-film transistor according to claim 9, wherein said insulating layer is a silicon oxide layer formed by oxidizing a surface of said channel region at a temperature of 500°C or below.

**Claims 12-21. (Canceled)**

22. (Previously Presented) The thin-film transistor according to claim 1, wherein said first insulating layer is a silicon oxide layer or a silicon oxynitride layer.

23. (New) A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate are a channel region, a source region, a drain region, a first insulating layer and a second insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

said glass substrate is defined as having a physical property such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute, and

said first insulating layer covers said channel region, and

said second insulating layer is formed on a surface of said first insulating layer.

24. (New) The thin-film transistor according to claim 23,

wherein said first insulating layer is a silicon oxide layer or a silicon oxynitride layer.

25. (New) A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate are a channel region, a source region, a drain region and an insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

said glass substrate is defined as having a physical property such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute, and

said insulating layer covers said channel region.

26. (New) The thin-film transistor according to claim 25,

wherein said insulating layer is a silicon oxide layer formed by oxidizing a surface of said channel region at a temperature of 500°C or below.